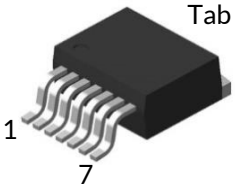
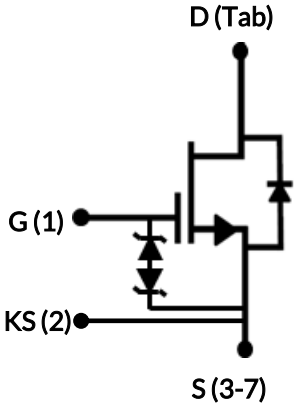
DATASHEET

UJ4SC075018B7S

750V-18mΩ SiC FET

Rev. A, January 2022





Part Number	Package	Marking
UJ4SC075018B7S	D^2PAK-7L	UJ4SC075018B7S

RoHS COMPLIANT | Pb LEAD FREE | HF HALOGEN FREE

Description

The UJ4SC075018B7S is a 750V, 18mΩ G4 SiC FET. It is based on a unique 'cascode' circuit configuration, in which a normally-on SiC JFET is co-packaged with a Si MOSFET to produce a normally-off SiC FET device. The device's standard gate-drive characteristics allows for a true "drop-in replacement" to Si IGBTs, Si FETs, SiC MOSFETs or Si superjunction devices. Available in the D^2PAK-7L package, this device exhibits ultra-low gate charge and exceptional reverse recovery characteristics, making it ideal for switching inductive loads and any application requiring standard gate drive.

Features

- On-resistance $R_{DS(on)}$: 18mΩ (typ)
- Operating temperature: 175°C (max)
- Excellent reverse recovery: Q_{rr} = 125nC
- Low body diode V_{FSD}: 1.14V
- Low gate charge: Q_G = 37.8nC
- Threshold voltage $V_{G(th)}$: 4.8V (typ) allowing 0 to 15V drive
- Low intrinsic capacitance
- ESD protected, HBM class 2
- D^2PAK-7L package for faster switching, clean gate waveforms

Typical applications

- EV charging
- PV inverters
- Switch mode power supplies
- Power factor correction modules
- Motor drives
- Induction heating

Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
Drain-source voltage	V_{DS}		750	V
Gate-source voltage	V_{GS}	DC	-20 to +20	V
		AC (f > 1Hz)	-25 to +25	V
Continuous drain current [1]	I_D	T_C = 25°C	72	A
		T_C = 100°C	52	A
Pulsed drain current [2]	I_{DM}	T_C = 25°C	208	A
Single pulsed avalanche energy [3]	E_{AS}	L=15mH, I_{AS} =3.6A	97.2	mJ
SiC FET dv/dt Ruggedness	dv/dt_{rug}	$V_{DS} \leq 500V$	200	V/ns
Power dissipation	P_{tot}	T_C = 25°C	259	W
Maximum junction temperature	$T_{J,max}$		175	°C
Operating and storage temperature	T_J, T_{STG}		-55 to 175	°C
Reflow soldering temperature	T_{solder}	reflow MSL 1	245	°C

1. Limited by $T_{J,max}$
2. Pulse width t_p limited by $T_{J,max}$
3. Starting T_J = 25°C

Thermal Characteristics

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Thermal resistance, junction-to-case	$R_{\theta JC}$			0.45	0.58	°C/W

Electrical Characteristics (T_J = +25°C unless otherwise specified)

Typical Performance - Static

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Drain-source breakdown voltage	BV_{DS}	V_{GS}=0V, I_D=1mA	750			V
Total drain leakage current	I_{DSS}	V_{DS}=750V, V_{GS}=0V, T_J=25°C		1.3	45	µA
		V_{DS}=750V, V_{GS}=0V, T_J=175°C		20		
Total gate leakage current	I_{GSS}	V_{DS}=0V, T_J=25°C, V_{GS}=-20V / +20V		4.7	± 20	µA
Drain-source on-resistance	$R_{DS(on)}$	V_{GS}=12V, I_D=50A, T_J=25°C		18	23	mΩ
		V_{GS}=12V, I_D=50A, T_J=125°C		29		
		V_{GS}=12V, I_D=50A, T_J=175°C		37		
Gate threshold voltage	$V_{G(th)}$	V_{DS}=5V, I_D=10mA	4	4.8	6	V
Gate resistance	R_G	f=1MHz, open drain		4.5		Ω

Typical Performance - Reverse Diode

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Diode continuous forward current [1]	I_S	T_C=25°C			72	A
Diode pulse current [2]	$I_{S,pulse}$	T_C=25°C			208	A
Forward voltage	V_{FSD}	V_{GS}=0V, I_F=20A, T_J=25°C		1.14	1.46	V
		V_{GS}=0V, I_F=20A, T_J=175°C		1.35		
Reverse recovery charge	Q_{rr}	V_{DS}=400V, I_S=50A, V_{GS}=-0V, R_{G_EXT}=50Ω di/dt=1400A/µs, T_J=25°C		125		nC
Reverse recovery time	t_{rr}			12.5		ns
Reverse recovery charge	Q_{rr}	V_{DS}=400V, I_S=50A, V_{GS}=-0V, R_{G_EXT}=50Ω di/dt=1400A/µs, T_J=150°C		128		nC
Reverse recovery time	t_{rr}			14.4		ns

Typical Performance - Dynamic

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Input capacitance	C_{iss}	V_{DS}=400V, V_{GS}=0V f=100kHz		1414		pF
Output capacitance	C_{oss}			118		
Reverse transfer capacitance	C_{rss}			2		
Effective output capacitance, energy related	$C_{oss(er)}$	V_{DS}=0V to 400V, V_{GS}=0V		150		pF
Effective output capacitance, time related	$C_{oss(tr)}$	V_{DS}=0V to 400V, V_{GS}=0V		280		pF
C_{OSS} stored energy	E_{oss}	V_{DS}=400V, V_{GS}=0V		12		µJ
Total gate charge	Q_G	V_{DS}=400V, I_D=50A, V_{GS} = 0V to15V		37.8		nC
Gate-drain charge	Q_{GD}			8		
Gate-source charge	Q_{GS}			11.8		
Turn-on delay time	$t_{d(on)}$	Note 4, V_{DS}=400V, I_D=50A, Gate Driver = 0V to +15V, Turn-on $R_{G,EXT}$=1Ω, Turn-off $R_{G,EXT}$=50Ω Inductive Load, FWD: same device with V_{GS} = 0V, R_G = 50Ω, T_J=25°C		13		ns
Rise time	t_r			23		
Turn-off delay time	$t_{d(off)}$			136		
Fall time	t_f			17.6		
Turn-on energy	E_{ON}			209		µJ
Turn-off energy	E_{OFF}			212		
Total switching energy	E_{TOTAL}			421		
Turn-on delay time	$t_{d(on)}$	Note 4, V_{DS}=400V, I_D=50A, Gate Driver = 0V to +15V, Turn-on $R_{G,EXT}$=1Ω, Turn-off $R_{G,EXT}$=50Ω Inductive Load, FWD: same device with V_{GS} = 0V, R_G = 50Ω, T_J=150°C		10.5		ns
Rise time	t_r			26		
Turn-off delay time	$t_{d(off)}$			146		
Fall time	t_f			20		
Turn-on energy	E_{ON}			245		µJ
Turn-off energy	E_{OFF}			248		
Total switching energy	E_{TOTAL}			493		

4. Measured with the half-bridge mode switching test circuit in Figure 23.

Typical Performance - Dynamic (continued)

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Turn-on delay time	$t_{d(on)}$	Note 5 and 6, V_{DS}=400V, I_D=50A, Gate Driver =0V to +15V, $R_{G,EXT}$=1Ω, inductive Load, FWD: same device with V_{GS} = 0V and R_G = 1Ω, RC snubber: R_S=10Ω and C_S=300pF, T_J=25°C		19		ns
Rise time	t_r			27		
Turn-off delay time	$t_{d(off)}$			41.6		
Fall time	t_f			10.4		
Turn-on energy including R_S energy	E_{ON}			169		µJ
Turn-off energy including R_S energy	E_{OFF}			149		
Total switching energy	E_{TOTAL}			318		
Snubber R_S energy during turn-on	E_{RS_ON}			5		
Snubber R_S energy during turn-off	E_{RS_OFF}			8.5		
Turn-on delay time	$t_{d(on)}$	Note 5 and 6, V_{DS}=400V, I_D=50A, Gate Driver =0V to +15V, $R_{G,EXT}$=1Ω, inductive Load, FWD: same device with V_{GS} = 0V and R_G = 1Ω, RC snubber: R_S=10Ω and C_S=300pF, T_J=150°C		17		ns
Rise time	t_r			29		
Turn-off delay time	$t_{d(off)}$			41		
Fall time	t_f			9		
Turn-on energy including R_S energy	E_{ON}			198		µJ
Turn-off energy including R_S energy	E_{OFF}			153		
Total switching energy	E_{TOTAL}			351		
Snubber R_S energy during turn-on	E_{RS_ON}			5		
Snubber R_S energy during turn-off	E_{RS_OFF}			7		

5. Measured with the switching test circuit in Figure 24.
6. In this datasheet, all the switching energies (turn-on energy, turn-off energy and total energy) presented in the tables and Figures include the device RC snubber energy losses.

Typical Performance Diagrams

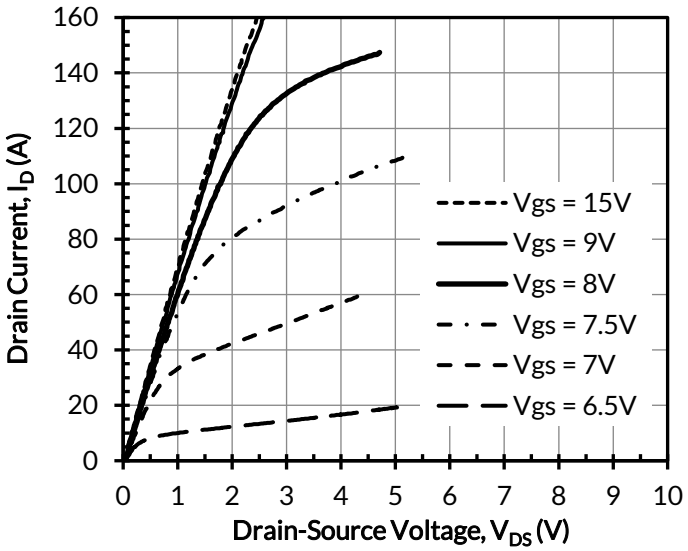


Figure 1. Typical output characteristics at T_J = - 55°C, tp < 250µs

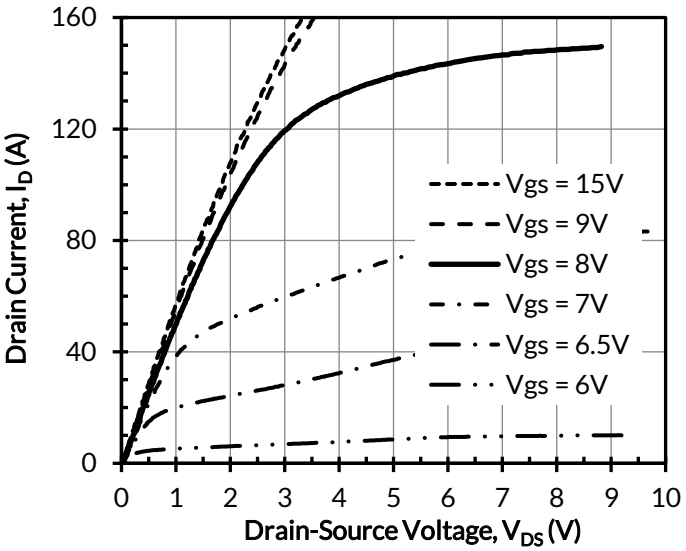


Figure 2. Typical output characteristics at T_J = 25°C, tp < 250µs

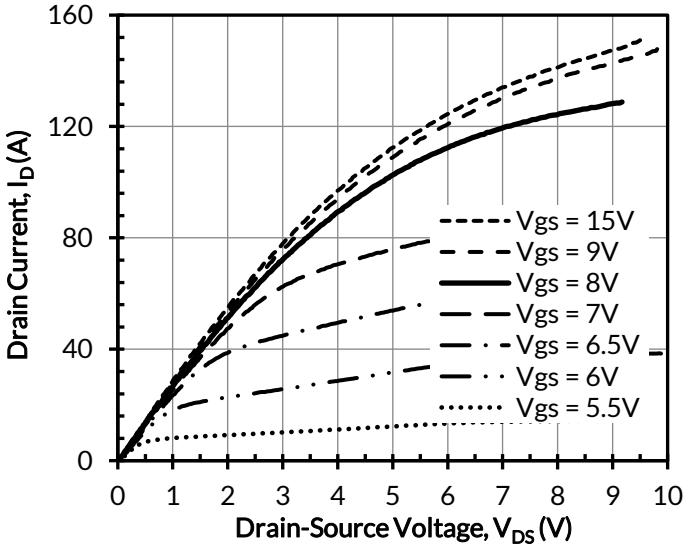


Figure 3. Typical output characteristics at T_J = 175°C, tp < 250µs

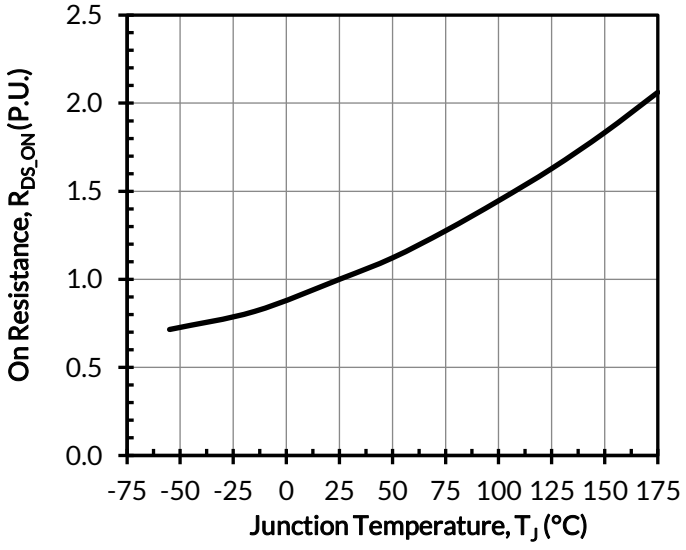


Figure 4. Normalized on-resistance vs. temperature at V_{GS} = 12V and I_D = 50A

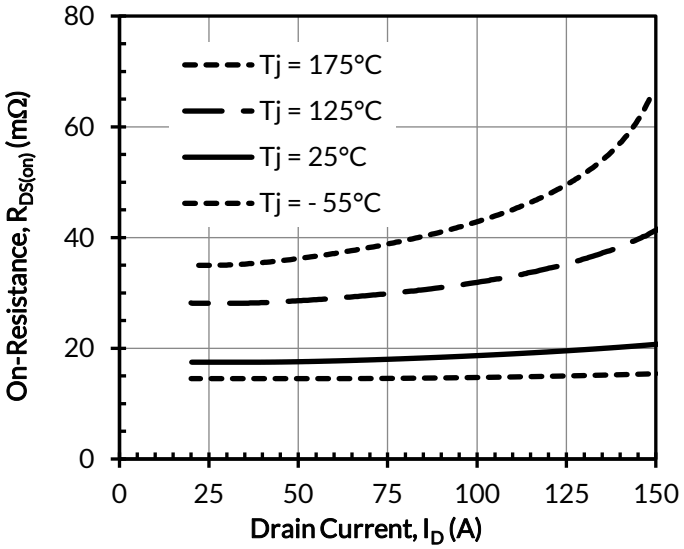


Figure 5. Typical drain-source on-resistances at V_{GS} = 12V

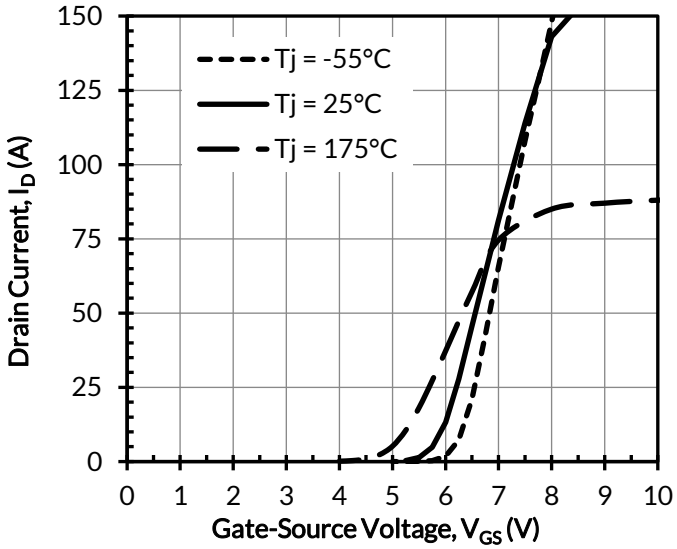


Figure 6. Typical transfer characteristics at V_{DS} = 5V

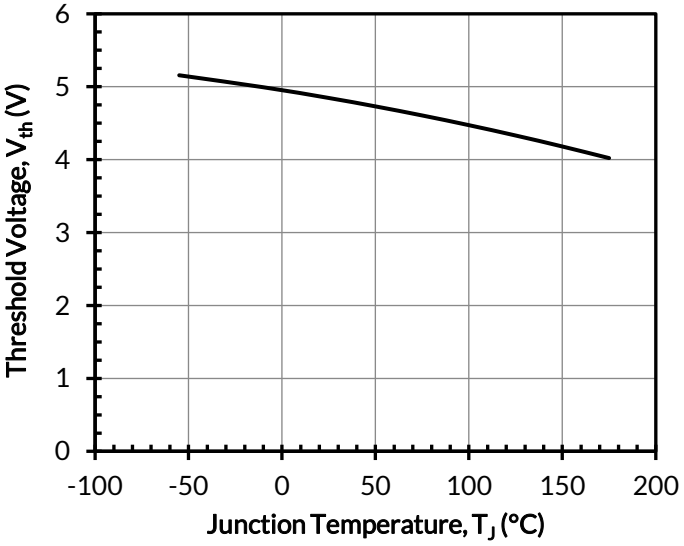


Figure 7. Threshold voltage vs. junction temperature at V_{DS} = 5V and I_D = 10mA

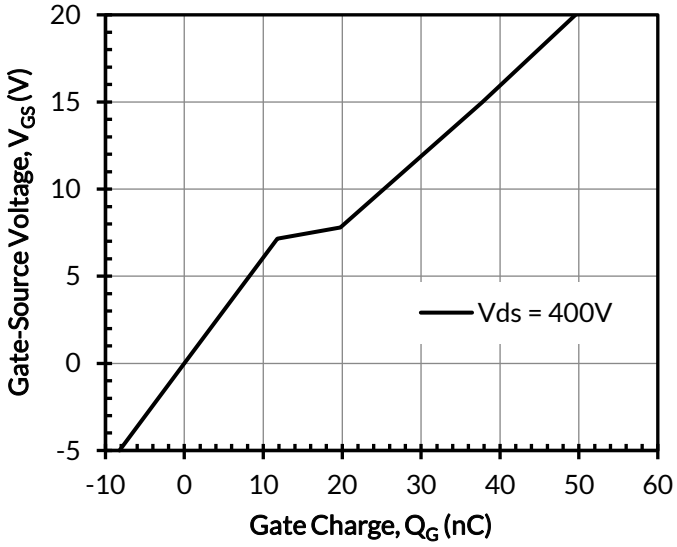


Figure 8. Typical gate charge at I_D = 50A

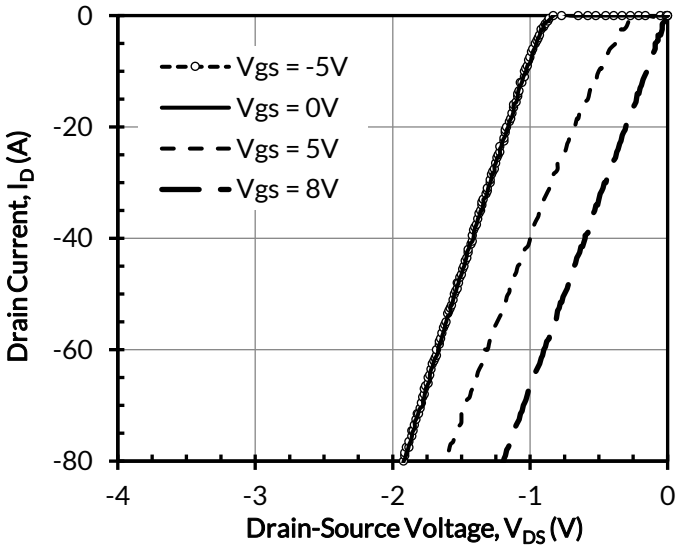


Figure 9. 3rd quadrant characteristics at T_J = -55°C

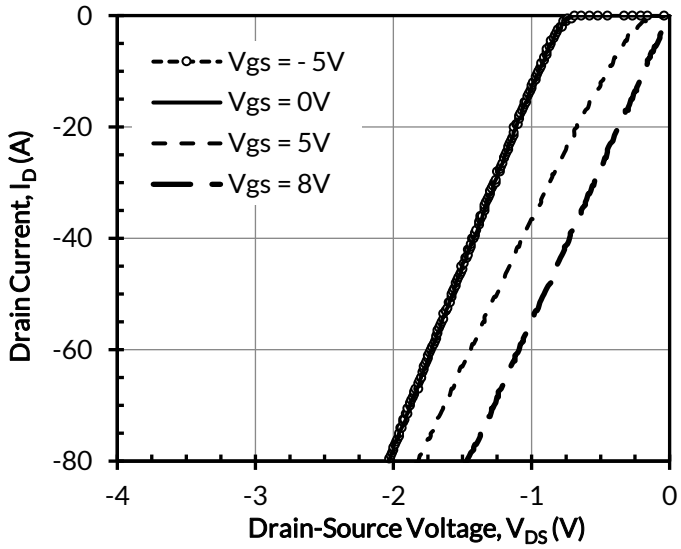


Figure 10. 3rd quadrant characteristics at T_J = 25°C

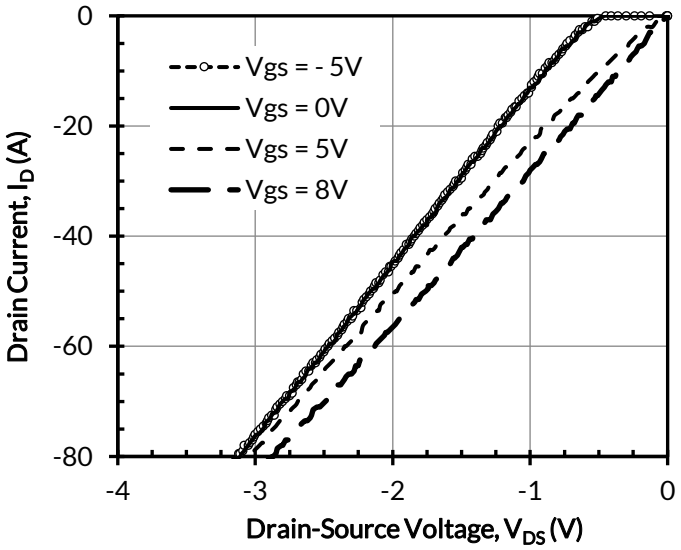


Figure 11. 3rd quadrant characteristics at T_J = 175°C

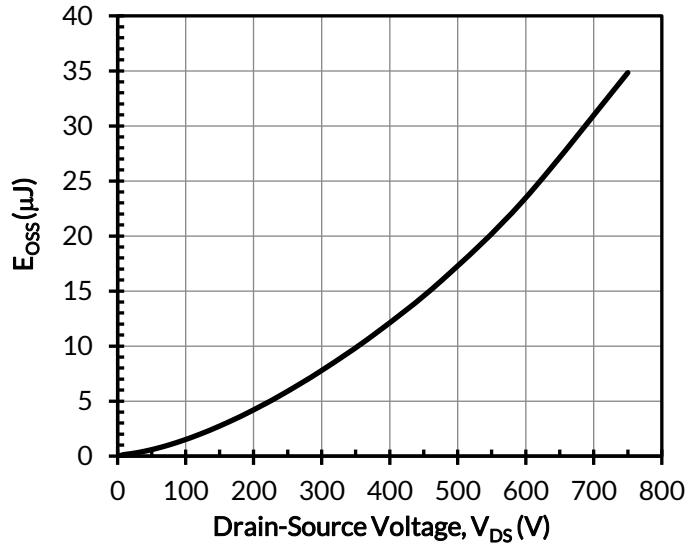


Figure 12. Typical stored energy in C_{OSS} at V_{GS} = 0V

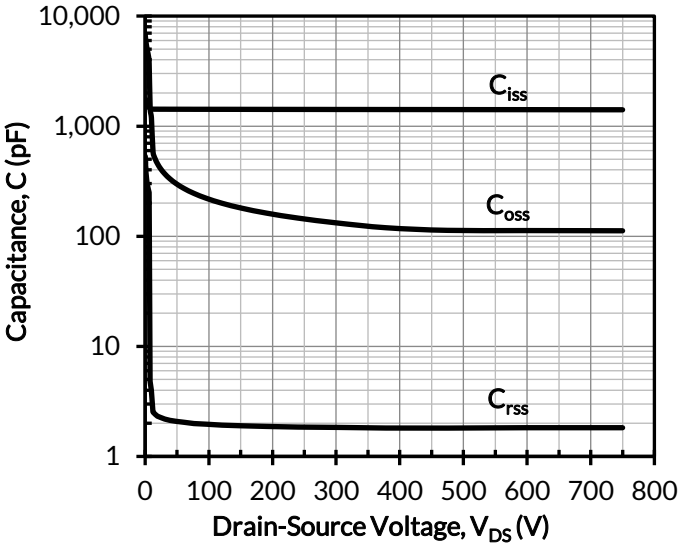


Figure 13. Typical capacitances at f = 100kHz and V_{GS} = 0V

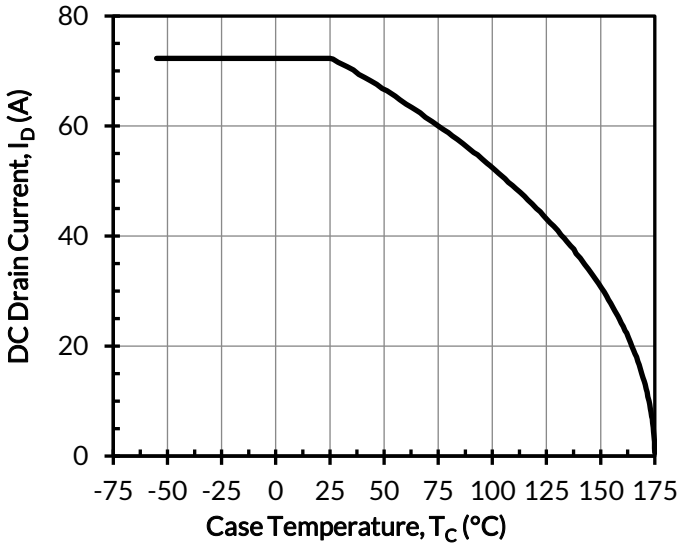


Figure 14. DC drain current derating

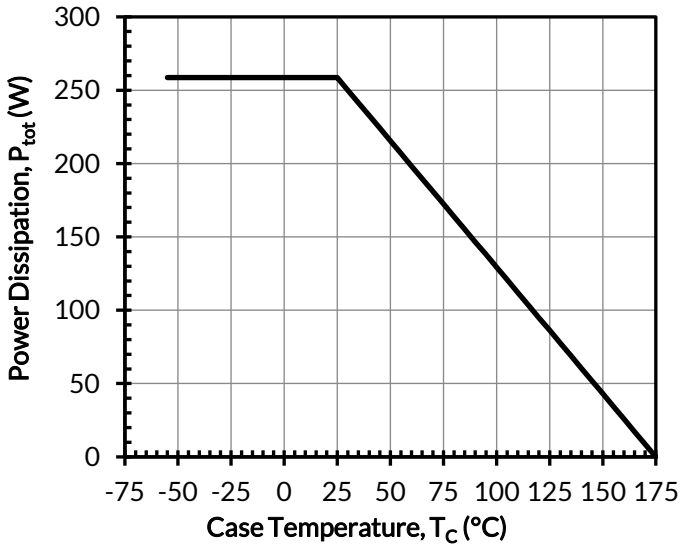


Figure 15. Total power dissipation

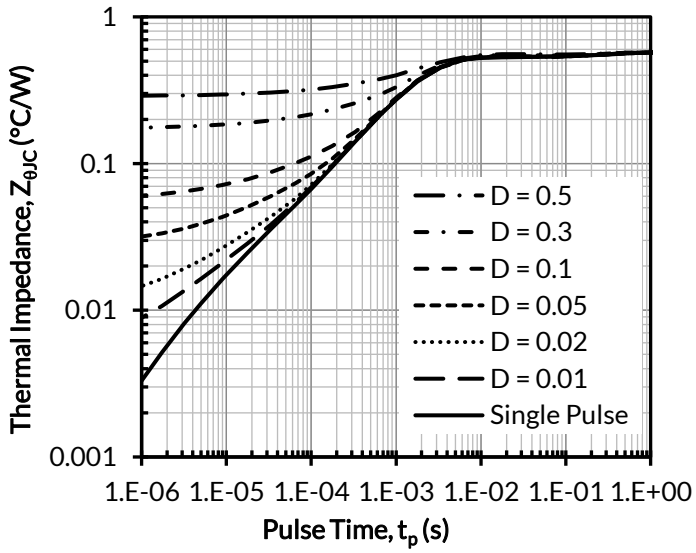


Figure 16. Maximum transient thermal impedance

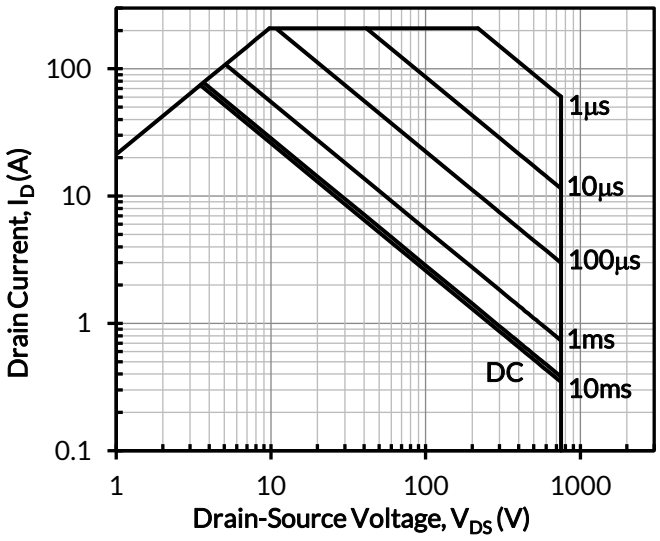


Figure 17. Safe operation area at T_C = 25°C, D = 0, Parameter t_p

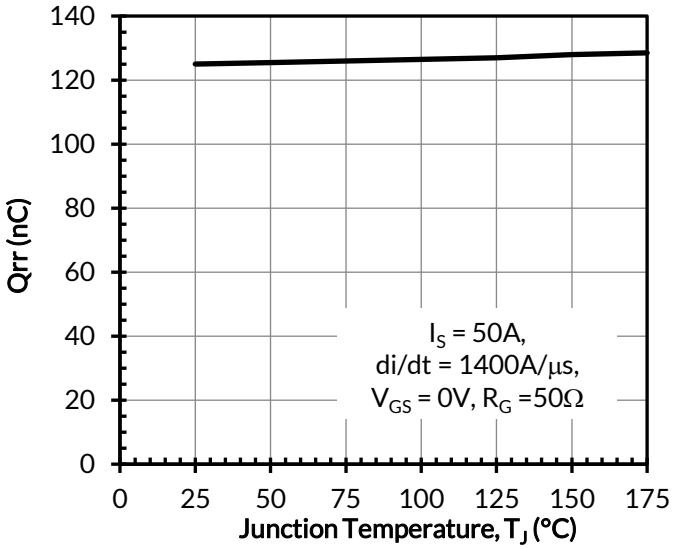


Figure 18. Reverse recovery charge Qrr vs. junction temperature at Vds = 400V

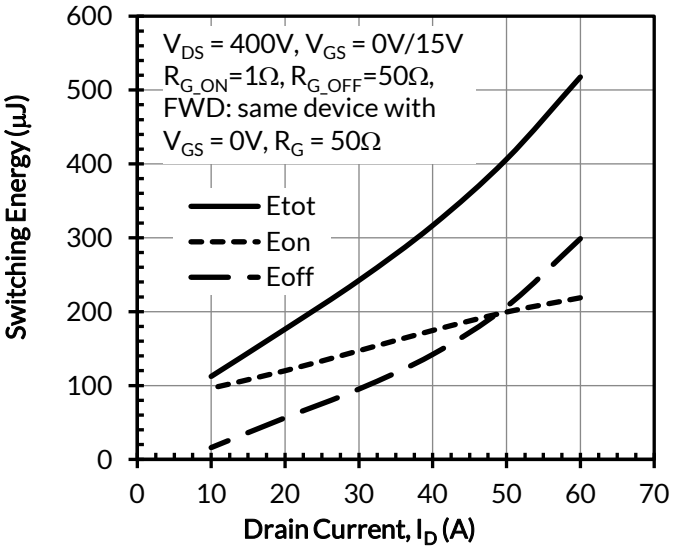


Figure 19. Clamped inductive switching energy vs. drain current at V_{DS} = 400V and T_J = 25°C

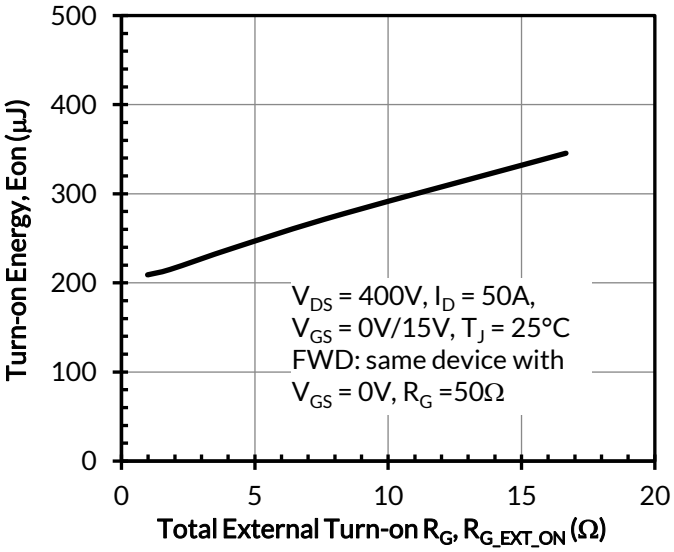


Figure 20. Clamped inductive switching turn-on energy vs. R_{G,EXT_ON}

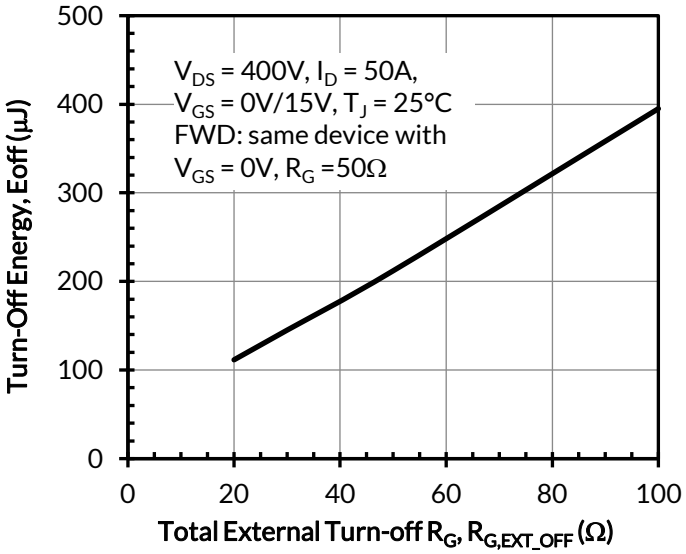


Figure 21. Clamped inductive switching turn-off energy vs. R_{G,EXT_OFF}

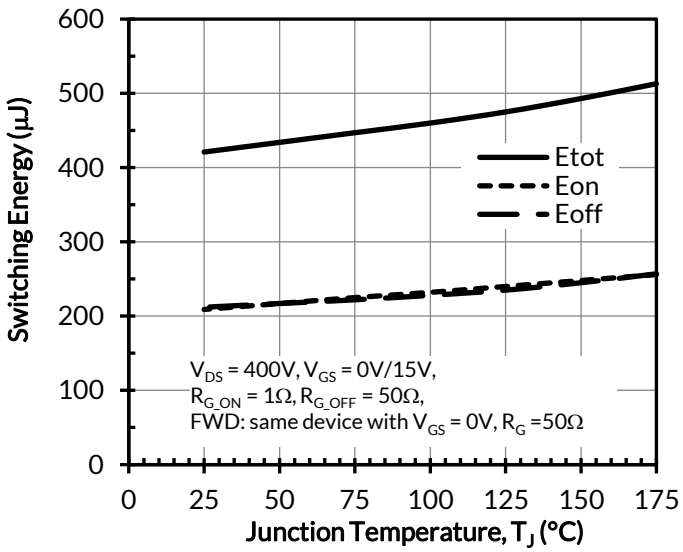


Figure 22. Clamped inductive switching energy vs. junction temperature at V_{DS} =400V and I_D = 50A

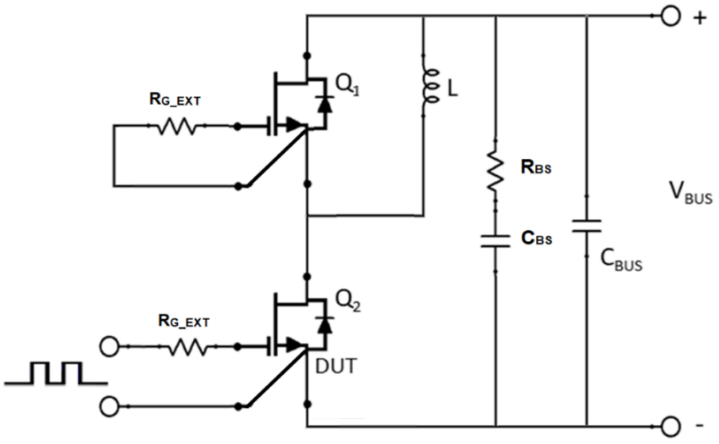


Figure 23. Schematic of the half-bridge mode switching test circuit. Note, a bus RC snubber (R_{BS} = 2.5Ω, C_{BS}=100nF) is used to reduce the power loop high frequency oscillations.

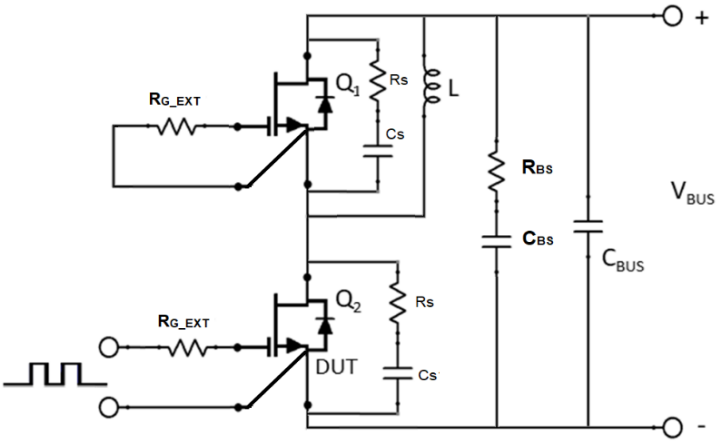


Figure 24.Schematic of the half-bridge mode switching test circuit with device RC snubbers (Rs =10Ω, Cs = 300pF) and a bus RC snubber (R_{BS} = 2.5Ω, C_{BS}=100nF).